

ABSTRACT OF THE DISCLOSURE

A piezoelectric oxide single crystal wafer, wherein number of particles adhering to a surface of the wafer and having a size of 1 μm or more is 85 or less per mm^2 . The piezoelectric oxide single crystal wafer consists of any one of lithium tantalate, lithium niobate, quartz crystal, lithium tetraborate and langasite, and suitably used for production of surface acoustic wave filters. The piezoelectric oxide single crystal wafer of the present invention enables fine electrode formation and device production with good yield.